KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR TECHNICAL DATA

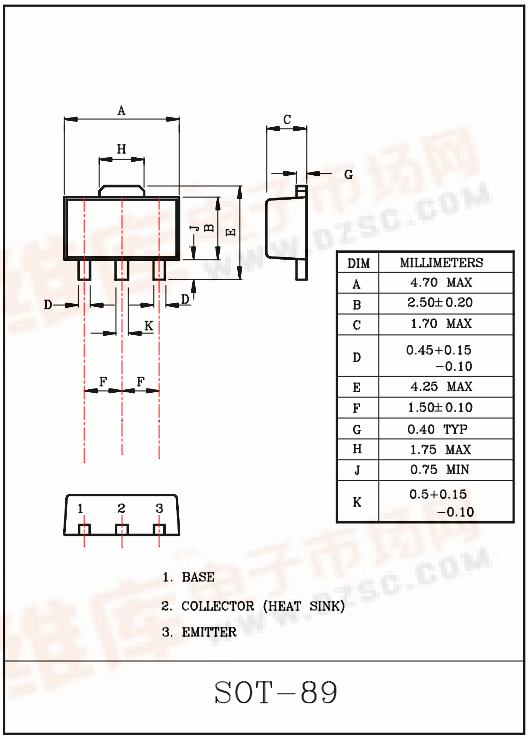
KTA1662

EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.

FEATURES

- 1W (Mounted on Ceramic Substrate).
- Small Flat Package.
- Complementary to KTC4374.



DIM	MILLIMETERS
A	4.70 MAX
B	2.50±0.20
C	1.70 MAX
D	0.45+0.15 −0.10
E	4.25 MAX
F	1.50±0.10
G	0.40 TYP
H	1.75 MAX
J	0.75 MIN
K	0.5+0.15 −0.10

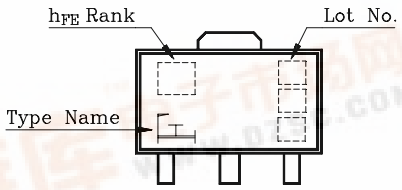
SOT-89

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-400	mA
Base Current	I_B	-80	mA
Collector Power Dissipation	P_C	500	mW
	P_C*	1	W
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

P_C* : KTA1662 mounted on ceramic substrate ($250mm^2$x0.8t)

Marking

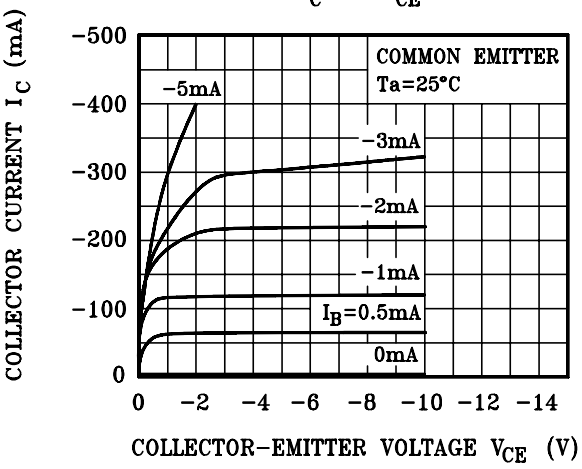


ELECTRICAL CHARACTERISTICS (Ta=25℃)

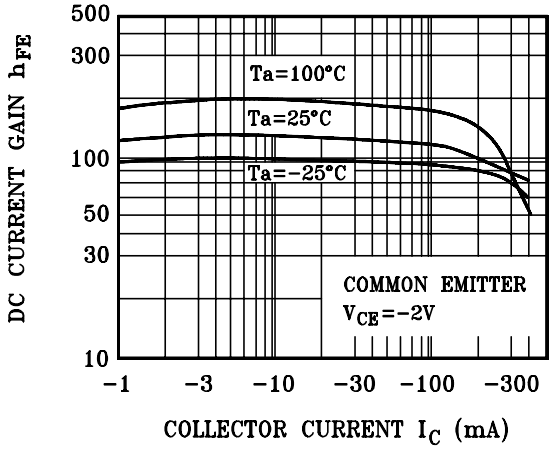
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-80V, I_E=0	-	-	-100	nA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-100	nA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=-10mA, I_B=0	-80	-	-	V
DC Current Gain	h_{FE}(1) (Note)	V_{CE}=-2V, I_C=-50mA	70	-	240	
	h_{FE}(2)	V_{CE}=-2V, I_C=-200mA	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-200mA, I_B=-20mA	-	-	-0.4	V
Base-Emitter Voltage	V_{BE}	V_{BE}=-2V, I_C=-5mA	-0.55	-	-0.8	V
Transition Frequency	f_T	V_{CE}=-10V, I_C=-10mA	-	120	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	14	-	pF

Note : h_{FE} Classification O:70~140, Y:120~240

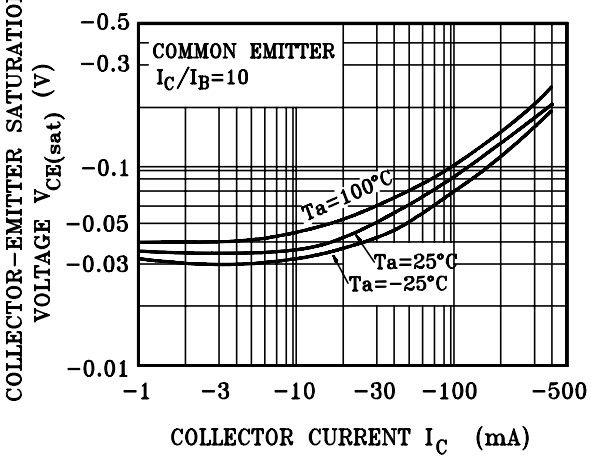
I_C – V_{CE}



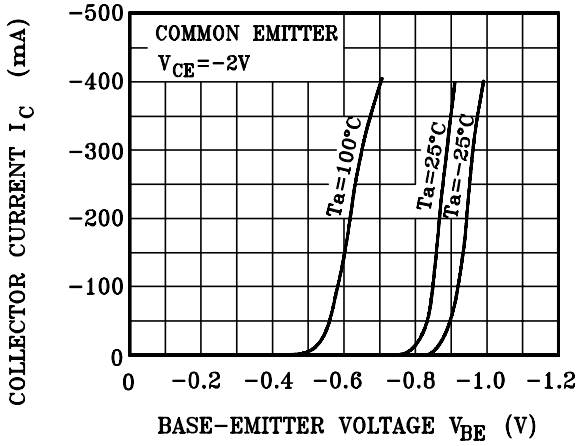
h_{FE} – I_C



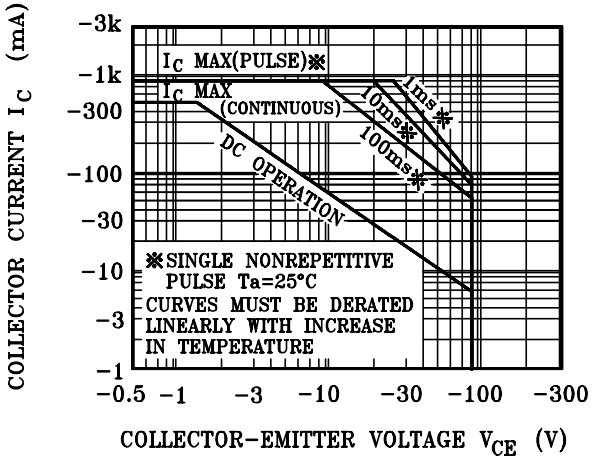
$V_{CE(sat)}$ – I_C



I_C – V_{BE}



SAFE OPERATING AREA



P_C – Ta